Test wafer: 6-inch Si wafer with 1um SiO2 on top (thermal oxidation)

Stepper reticle mask: line width 520 nm, pitch 3000 nm

Exposure dose 205 J/m2

ICP etch: (1) pxBracEtchtry1 30s

(2) C4F8/H2 8/30sccm, 3mTorr, 1000/200W, 20oC, 9mins30sec

All the SEM images were taken with the DUV resist after dry etch.









